

/ Descriptions

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

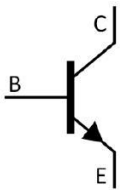
/ Features

h_{FE} ,
Low noise, high h_{FE} , high breakdown voltage.

/ Applications

Low noise audio amplifier application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	Y	GR	BL
h_{FE} Range	120~240	200~400	350~700

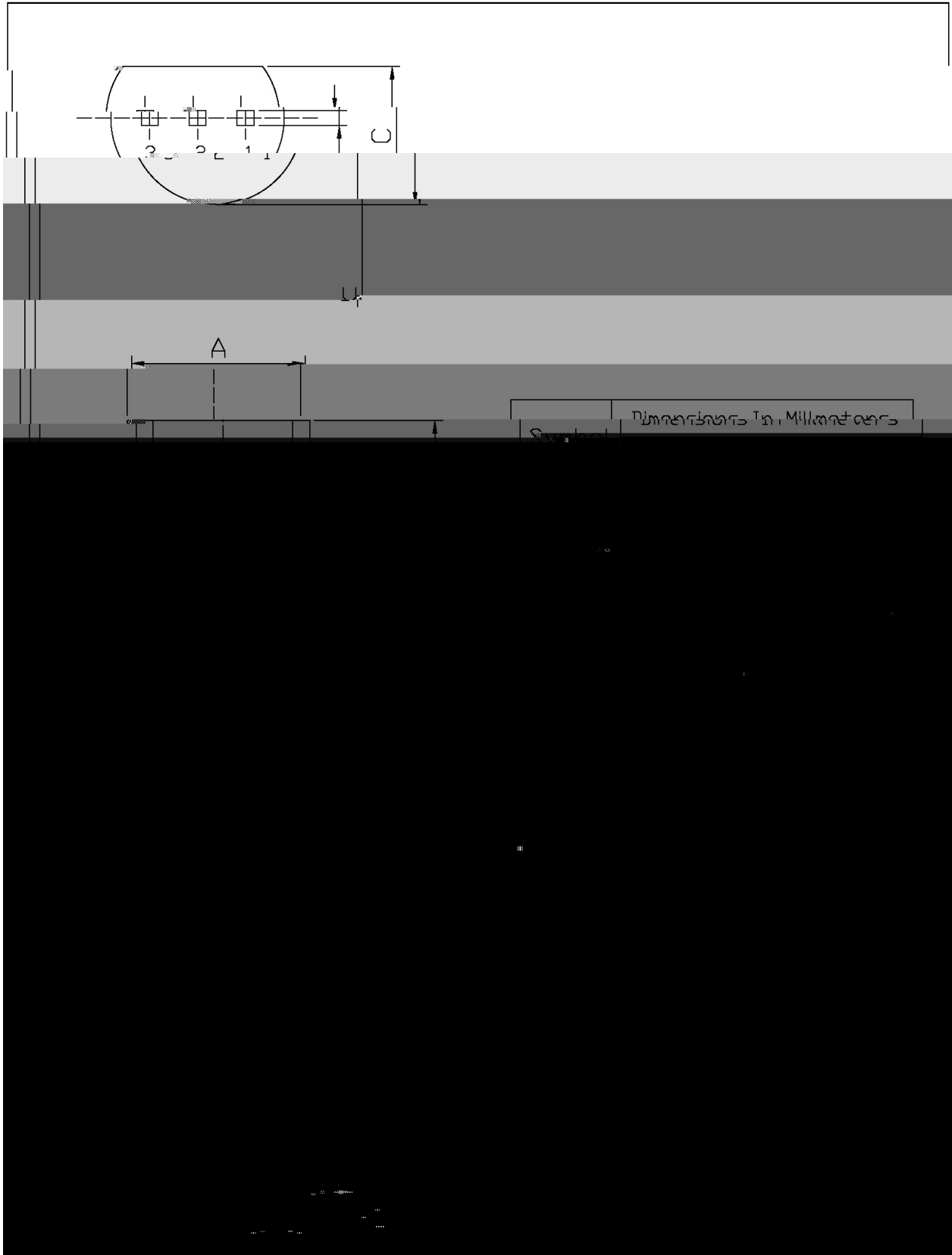
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	120	V
Collector to Emitter Voltage	V_{CEO}	120	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=1.0mA$ $I_B=0$	120			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=100\mu A$ $I_E=0$	120			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=100\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I					

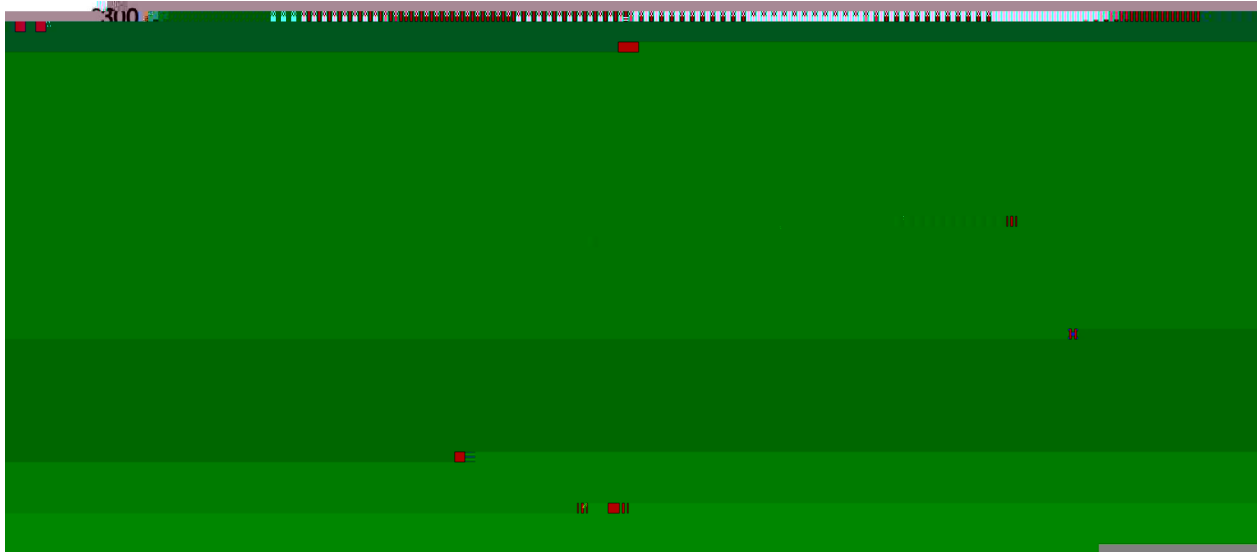
/ Package Dimensions

T0-92

Unit: mm



() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

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